BTC1510F3

Preliminary

NPN SILICON TRANSISTOR

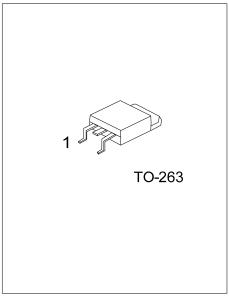
NPN EPITAXIAL PLANAR TRANSISTOR

■ DESCRIPTION

As a NPN Darlington transistor the UTC **BTC1510F3** is designed for general purpose amplifier and low speed switching application.

■ FEATURES

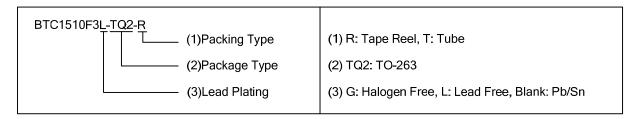
- * Very high BV_{CEO}
- * Very low $V_{\text{CE(SAT)}}$
- * Very high current gain



Lead-free: BTC1510F3L Halogen-free: BTC1510F3G

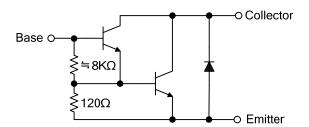
ORDERING INFORMATION

Ordering Number			Dookogo	Pin Assignment			Dooking	
Normal	Lead Free	Halogen Free	Package	1	2	3	Packing	
BTC1510F3-TQ2-R	BTC1510F3L-TQ2-R	BTC1510F3G-TQ2-R	TO-263	В	С	Е	Tape Reel	
BTC1510F3-TQ2-T	BTC1510F3L-TQ2-T	BTC1510F3G-TQ2-T	TO-263	В	С	Е	Tube	



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■ EQUIVALENT CIRCUIT



■ ABSOLUTE MAXIMUM RATING (T_a=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage	V_{CBO}	150	V		
Collector-Emitter Voltage		V_{CEO}	150	V	
Emitter-Base Voltage		V_{EBO}	5	V	
Collector Current	DC	Ic	10	Λ	
Collector Gurrent	Pulse(Note 2)	ic	15	Α	
Collector Dissipation	T _a =25°℃	P_D	2	W	
Collector Dissipation	T _C =25°C	ı D	60		
Junction Temperature	T _J	150	$^{\circ}\!\mathbb{C}$		
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\mathbb{C}$		

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse test: Pulse Width=100ms

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA, I _E =0	150			V	
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	150			V	
Door Fraitter Turn On Voltone (Note)	V _{BE(ON)}	V _{CE} =3V, I _C =5A			2.8	\ \	
Base-Emitter Turn-On Voltage (Note)		$V_{CE}=3V$, $I_{C}=10A$			4.5	V	
	V_{FEC}	I _C =5A			3	V	
Collector Cutoff Current	I_{CBO}	V _{CB} =150V, I _E =0			200	μΑ	
Collector Cutoff Current	I _{CEO}	V _{CE} =150V, I _E =0			200	μΑ	
Emitter Cutoff Current	I _{EBO}	$V_{EB}=5V$, $I_{C}=0$			2	mA	
ON CHARACTERISTICS							
DC Current Gain (Note)	h _{FE}	V _{CE} =3V, I _C =5A	2		20	K	
Do Guiletti Gaiii (Note)		$V_{CE}=3V$, $I_{C}=10A$	100				
Base-Emitter Saturation Voltage(Note)	$V_{BE(SAT)}$	I _C =5A, I _B =5mA			2	V	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I _C =5A, I _B =10mA			1.5		
(Note)		I _C =10A, I _B =100mA			3	V	
(Note)		I _C =5A, I _B =2.5mA			2		

Note: Pulse test: Pulse Width \leq 380 μ s, Duty Cycle \leq 2%

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